

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A process for the catalytic hydrodehalogenation of SiCl_4 to form HSiCl_3 ,

which comprises bringing a gaseous feed mixture comprising hydrogen and silicon tetrachloride into direct contact with at least one heating element of a resistance heating device, with the heating element being composed of a metal or a metal alloy and being heated to carry out the reaction.

Claim 2 (Original): The process as claimed in claim 1,
characterized in that
at least one heating element composed of a metal from the group consisting of niobium, tantalum and tungsten or of a metal alloy comprising niobium, tantalum and/or tungsten is used.

Claim 3 (Currently Amended): The process as claimed in claim 1 [[or 2]],
characterized in that
at least one heating element which has the form of a wire, a spiral, a web, a tube, a plate, a mesh or a honeycomb body is used.

Claim 4 (Currently Amended): The process as claimed in ~~any of claims 1 to 3~~ claim
1,
characterized in that
a heating element whose wire diameter, wall thickness or plate or layer thickness is from 0.1 mm to 10 mm is used.

Claim 5 (Currently Amended): The process as claimed in ~~any of claims 1 to 4~~ claim
1,
characterized in that
the heating elements of the resistance heating device are operated at a temperature in
the range from 300 to 1250°C.

Claim 6 (Currently Amended): The process as claimed in ~~any of claims 1 to 5~~ claim
1,
characterized in that
the reaction is carried out at a temperature in the range from 600 to 950°C and a
pressure of from 0.1 to 100 bar abs.

Claim 7 (Currently Amended): The process as claimed in ~~any of claims 1 to 6~~ claim
1,
characterized in that
the reaction is carried out at a space velocity of from 2000 to 750 000 h⁻¹ and the gas
mixture of hydrogen and silicon tetrachloride is passed over the heating elements of the
resistance heating device at a linear velocity of from 0.01 to 10 m/s.

Claim 8 (Currently Amended): The process as claimed in ~~any of claims 1 to 7~~ claim
7,
characterized in that
an SiCl₄/H₂ mixture having a molar ratio of from 1:0.9 to 1:20 is used.

Claim 9 (Currently Amended): The process as claimed in ~~any of claims 1 to 8~~ claim 7,
characterized in that
the degree of conversion is set by setting the electric power of the resistance heating device.

Claim 10 (Currently Amended): The process as claimed in ~~any of claims 1 to 9~~ claim 1,
characterized in that
the reaction is carried out in a flow reactor whose walls or wall insides are composed of niobium, tungsten, tantalum, a niobium , tungsten and/or tantalum-containing alloy, a heat-resistant glass, fused silica, a heat-resistant glaze or a heat-resistant ceramic.

Claim 11 (Currently Amended): The process as claimed in ~~any of claims 1 to 10~~ claim 7,
characterized in that
the product mixture is passed through at least one heat exchanger located at the beginning of the process in order to vaporize SiCl_4 and/or preheat the H_2/SiCl_4 -containing feed mixture.

Claim 12 (Currently Amended): The process as claimed in ~~any of claims 1 to 11~~ claim 11,
characterized in that

(i) the product mixture is at least partially condensed, liquid HSiCl_3 is isolated and any hydrogen and silicon tetrachloride obtained are recirculated to the feed stream to the process or (ii) the product stream is passed as starting material to a further use.